

L Number	Hits	Search Text	DB	Time stamp
1	88	effusion near3 cell same (MBE or molecular adj beam adj epitax\$3) and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 09:40
2	13	effusion near3 cell same (MBE or molecular adj beam adj epitax\$3) same crucible and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 10:00
4	3	effusion near3 cell same (MBE or molecular adj beam adj epitax\$3) same temperature near2 rate and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 10:12
5	20	effusion near3 cell near4 temperature same (MBE or molecular adj beam adj epitax\$3) and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 10:13
-	93	fullerene near2 buckminster	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 14:32
-	2	fullerene near2 buckminster same carbon near2 source	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 14:33
-	25	(fullerene same carbon near2 source) and MBE	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 14:34
-	2	fullerene same MBE	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 14:37
-	80	fullerene same carbon near2 source	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 14:38
-	59	fullerene near15 carbon near2 source	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:36
-	59	(silicon adj carbide or sic) same (MBE or molecular adj beam adj epitax\$4) and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 15:29
-	32	(MBE or molecular adj beam adj epitax\$4) and ((si or silicon) near3 source same (Carbon or C) near3 source) and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 15:33
-	1	(MBE or molecular adj beam adj epitax\$4) and ((si or silicon) near3 source near3 solid same (Carbon or C) near3 source) and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 15:36

	3	(fullerene near15 carbon near2 source) and (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:13
	4	solid near4 (silicon or si) near5 source same crucible same (sic or silicon adj carbide) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:15
	1	solid near4 (silicon or si) same crucible same (sic or silicon adj carbide) near4 coat\$3 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:17
	9	solid near4 (silicon or si) same crucible near7 (sic or silicon adj carbide) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:20
	3	(silicon or si) near4 (source or solid) same crucible near7 (sic or silicon adj carbide) near4 coat\$3 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:22
	4	crucible near7 (sic or silicon adj carbide) near4 coat\$3 and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:25
	1	crucible near7 (sic or silicon adj carbide) near4 protect\$5 and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:26
	3	crucible near7 (sic or silicon adj carbide) near4 protect\$5 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:27
	26	fullerene near15 carbon near2 source same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:45
	29	fullerene same temperature and (MBE or molecular adj beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 17:47
	14	fullerene same temperature and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:01
	3	(Sic or silicon adj carbide) near3 (deposit\$4 or growth) and (CMP or chemical near2 mechanical near2 planar\$5) same substrate and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:04
	12	(CMP or chemical near2 mechanical near2 planar\$5) same substrate and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:07
	48	(CMP or chemical near2 mechanical near2 polish\$4) same substrate and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:14

	2	(CMP or chemical near2 mechanical near2 polish\$4) same (substrate or wafer) same (silicon adj carbide or sic) and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:16
	12	(CMP or chemical near2 mechanical near2 polish\$4) same (substrate or wafer) and (MBE or molecular adj beam adj epitax\$3) and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:17
	7	(CMP or chemical near2 mechanical near2 polish\$4) same (substrate or wafer) and (MBE or molecular adj beam adj epitax\$3) and 117/\$4.cccls. and (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:19
	3	(CMP or chemical near2 mechanical near2 polish\$4) same (silicon adj carbide or sic) and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:20
	12	(CMP or chemical near2 mechanical near2 polish\$4) same (silicon adj carbide or sic) near4 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:39
	1	electron near3 beam near3 gun same crucible and (MBE or molecular adj beam adj epitax\$3) and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:44
	7	electron near3 beam near3 gun same crucible and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:47
	10	electron near3 beam near3 gun same crucible and (MBE or molecular adj beam adj epitax\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/08 18:58
	9	solid near4 silicon near4 source same temperature and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 09:39